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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	TBA
<i>(use as many sheets as necessary)</i>				Filing Date	Herewith
Sheet	2	of	2	First Named Inventor	TAKEDA et al.
				Group Art Unit	TBA
				Examiner Name	TBA
				Attorney Docket Number	KOJIM-448

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
S.J. L.	L	International Work Shop 157nm Lithography MIT-LL, Boston, MA, May 5, 1999		T ²
	M	Kunz et al. "Outlook for 157 nm Resist Design," <i>J. Vac. Sci. Technol. B</i> 17(6), Nov/Dec 1999, pp. 3267-3272		
	N	Chiba et al., "157 nm Resist Materials: A Progress Report," <i>J. Photopolymer Science and Technology</i> , Vol. 13, No. 4 (2000) pp 657-664		
	O	Schmaljohann et al., "Fundamental Studies of Fluoropolymer Photoresists for 157 nm Lithography," <i>J. of Photopolymer Science Technology</i> , Vol., 13, No. 3 (2000) pp 451-458		
	P	Brunsvold et al., "Evaluation of a Deep UV Bilayer Resist for Sub-Half Micron Lithography," <i>SPIE</i> Vol. 1925 (1993), pp. 377-387		
	Q	Hatakeyama et al., "Investigation of Discrimination Enhancement in Polysilsesquioxane Based Positive Resist for ArF Lithography" <i>SPIE</i> Vol. 3333, pp. 62-72		
	R	Blakeney et al., "Evaluation of Materials for 193-nm Lithography" <i>J of Photopolymer Science and Technology</i> , Vol. 9, No. 3 (1996) pp 435-446		
	S	Kessel, et al., "novel Silicon-Containing Resists for EUV and 193 nm Lithography" <i>SPIE</i> Vol. 3678 (1999), pp. 214-220		
	T	Lin et al., "A High Resolution 248 nm Bilayer Resist" <i>SPIE</i> Vol. 3678 (1999) pp. 241250		
	U	Boardman et al., "Chemical Aspects of Silicon-Containing Bilayer Resists" <i>SPIE</i> Vol. 3678 (1999) pp. 562-572		
✓	V	Kim et al., "Chemically amplified resist based on the methacrylate polymer with 2-trimethylsilyl-2-propyl ester protecting group" <i>SPIE</i> Vol. 3678 (1999) pp 420-428		

Examiner Signature	<i>Sin J. Lee</i>	Date Considered	9-25-03
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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